(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
11 February 2010 (11.02.2010)

PCT

(10) International Publication Number
WO 2010/015467 A1

(51) **International Patent Classification**:
H01L 21/762 (2006.01)

(21) **International Application Number**:
PCT/EP2009/058434

(22) **International Filing Date**:
3 July 2009 (03.07.2009)

(25) **Filing Language**: English

(26) **Publication Language**: English

(30) **Priority Data**:
0855447 6 August 2008 (06.08.2008) FR

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(81) **Designated States** *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) **Designated States** *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

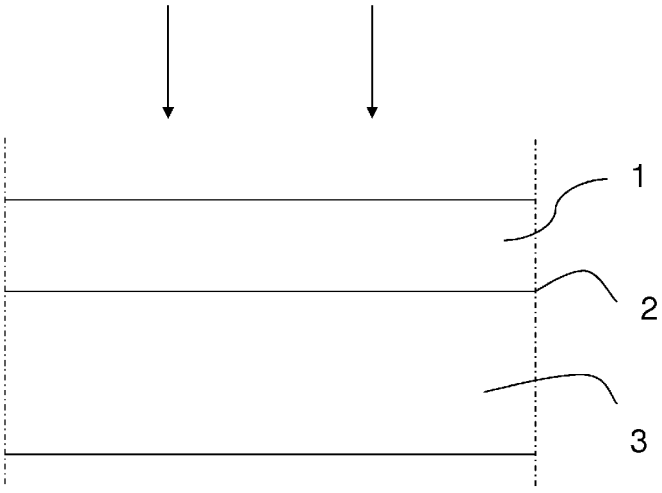
Declarations under Rule 4.17:

— *of inventorship (Rule 4.17(iv))*

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(54) **Title**: METHOD FOR MAKING A STRUCTURE COMPRISING A STEP FOR IMPLANTING IONS IN ORDER TO STABILIZE THE ADHESIVE BONDING INTERFACE

Figure 1



(57) **Abstract**: The present invention relates to a method for making a structure notably intended for applications in the fields of electronics, optics or optoelectronics, which comprises a thin layer (1) of semiconducting material on a supporting substrate (3), according to which: a) said thin layer (1) is adhesively bonded on said supporting substrate (3) by molecular adhesion; b) said thereby obtained structure is heat-treated in order to stabilize the adhesive bonding interface (2), characterized by the fact that prior to step b), it is proceeded with an implantation of ions at said interface (2), so as to transfer atoms from the thin layer (1) to the supporting substrate (3), and/or from the supporting substrate (3) to the thin layer (1).

WO 2010/015467 A1

Published:

— *with international search report (Art. 21(3))*